



# BSS84AKM

50 V, 230 mA P-channel Trench MOSFET

Rev. 1 — 23 May 2011

Product data sheet

## 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small SOT883 (SC-101) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

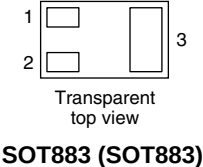
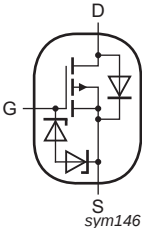
Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions                                                        | Min                   | Typ | Max  | Unit     |
|-------------------------------|----------------------------------|-------------------------------------------------------------------|-----------------------|-----|------|----------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25\text{ °C}$                                              | -                     | -   | -50  | V        |
| $V_{GS}$                      | gate-source voltage              |                                                                   | -20                   | -   | 20   | V        |
| $I_D$                         | drain current                    | $V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$                   | <a href="#">[1]</a> - | -   | -230 | mA       |
| <b>Static characteristics</b> |                                  |                                                                   |                       |     |      |          |
| $R_{DS(on)}$                  | drain-source on-state resistance | $V_{GS} = -10\text{ V}; I_D = -100\text{ mA}; T_j = 25\text{ °C}$ | -                     | 4.5 | 7.5  | $\Omega$ |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                                              | Graphic symbol                                                                                |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | G      | gate        | <br>Transparent<br>top view<br>SOT883 (SOT883) | <br>sym146 |
| 2   | S      | source      |                                                                                                                                 |                                                                                               |
| 3   | D      | drain       |                                                                                                                                 |                                                                                               |

3. Ordering information

Table 3. Ordering information

| Type number | Package |                                                                                  |         |
|-------------|---------|----------------------------------------------------------------------------------|---------|
|             | Name    | Description                                                                      | Version |
| BSS84AKM    | SOT883  | leadless ultra small plastic package; 3 solder lands;<br>body 1.0 x 0.6 x 0.5 mm | SOT883  |

4. Marking

Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| BSS84AKM    | ZA                          |

[1] % = placeholder for manufacturing site code

## 5. Limiting values

**Table 5. Limiting values**

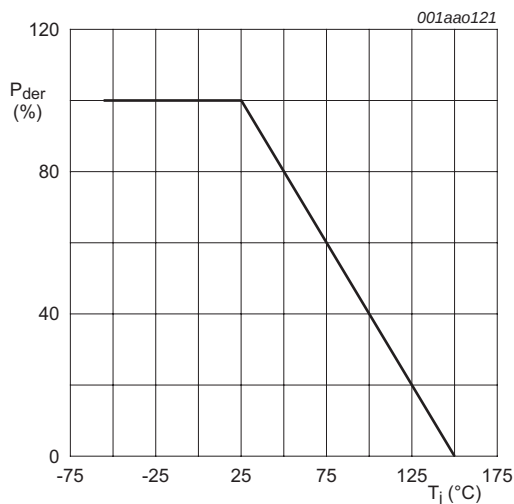
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                       | Conditions                                                                              | Min | Max  | Unit               |
|---------------------------|---------------------------------|-----------------------------------------------------------------------------------------|-----|------|--------------------|
| $V_{DS}$                  | drain-source voltage            | $T_J = 25\text{ }^{\circ}\text{C}$                                                      | -   | -50  | V                  |
| $V_{GS}$                  | gate-source voltage             |                                                                                         | -20 | 20   | V                  |
| $I_D$                     | drain current                   | $V_{GS} = -10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$                           | [1] | -    | -230 mA            |
|                           |                                 | $V_{GS} = -10\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$                          | [1] | -    | -150 mA            |
| $I_{DM}$                  | peak drain current              | $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; single pulse; $t_p \leq 10\text{ }\mu\text{s}$ | -   | -0.9 | A                  |
| $P_{tot}$                 | total power dissipation         | $T_{amb} = 25\text{ }^{\circ}\text{C}$                                                  | [2] | -    | 340 mW             |
|                           |                                 |                                                                                         | [1] | -    | 715 mW             |
|                           |                                 | $T_{sp} = 25\text{ }^{\circ}\text{C}$                                                   | -   | 2700 | mW                 |
| $T_J$                     | junction temperature            |                                                                                         | -55 | 150  | $^{\circ}\text{C}$ |
| $T_{amb}$                 | ambient temperature             |                                                                                         | -55 | 150  | $^{\circ}\text{C}$ |
| $T_{stg}$                 | storage temperature             |                                                                                         | -65 | 150  | $^{\circ}\text{C}$ |
| <b>Source-drain diode</b> |                                 |                                                                                         |     |      |                    |
| $I_S$                     | source current                  | $T_{amb} = 25\text{ }^{\circ}\text{C}$                                                  | [1] | -    | -230 mA            |
| <b>ESD maximum rating</b> |                                 |                                                                                         |     |      |                    |
| $V_{ESD}$                 | electrostatic discharge voltage | HBM                                                                                     | [3] | -    | 1000 V             |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

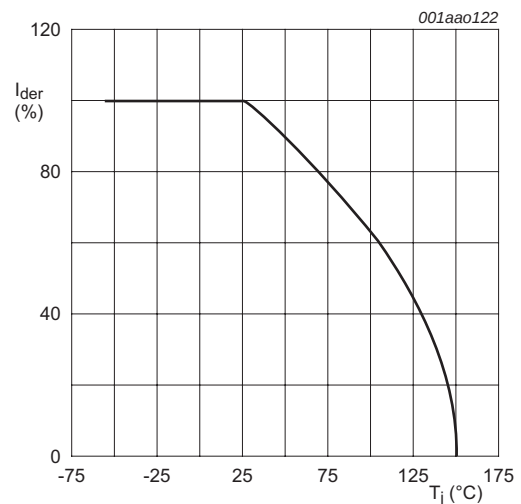
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



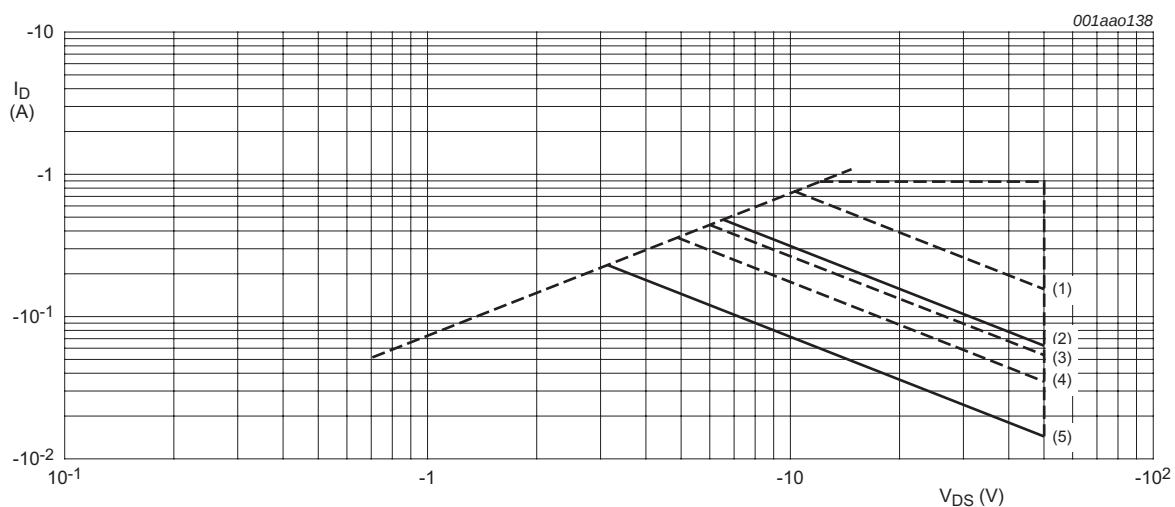
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of junction temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of junction temperature**



$I_{DM}$  is single pulse

(1)  $t_p = 1$  ms

(2) DC;  $T_{sp} = 25$  °C

(3)  $t_p = 10$  ms

(4)  $t_p = 100$  ms

(5) DC;  $T_{amb} = 25$  °C; drain mounting pad  $1$  cm<sup>2</sup>

**Fig 3.** Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions  | Min   | Typ | Max | Unit |
|----------------|--------------------------------------------------|-------------|-------|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] - | 310 | 360 | K/W  |
|                |                                                  |             | [2] - | 150 | 175 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -     | -   | 40  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

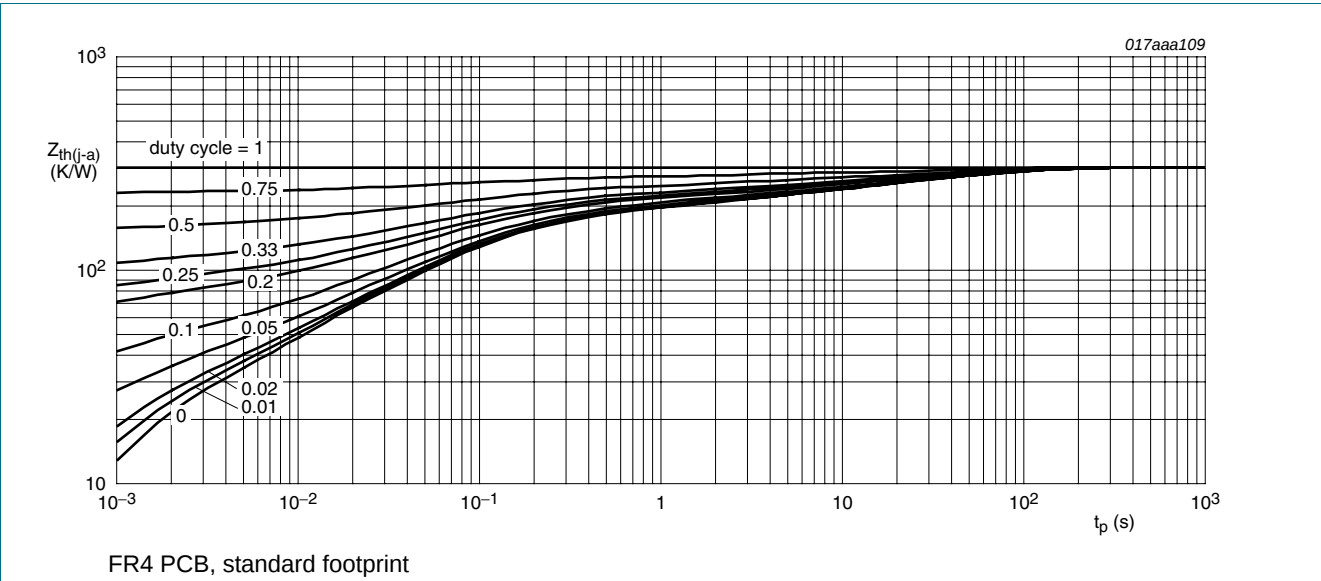


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

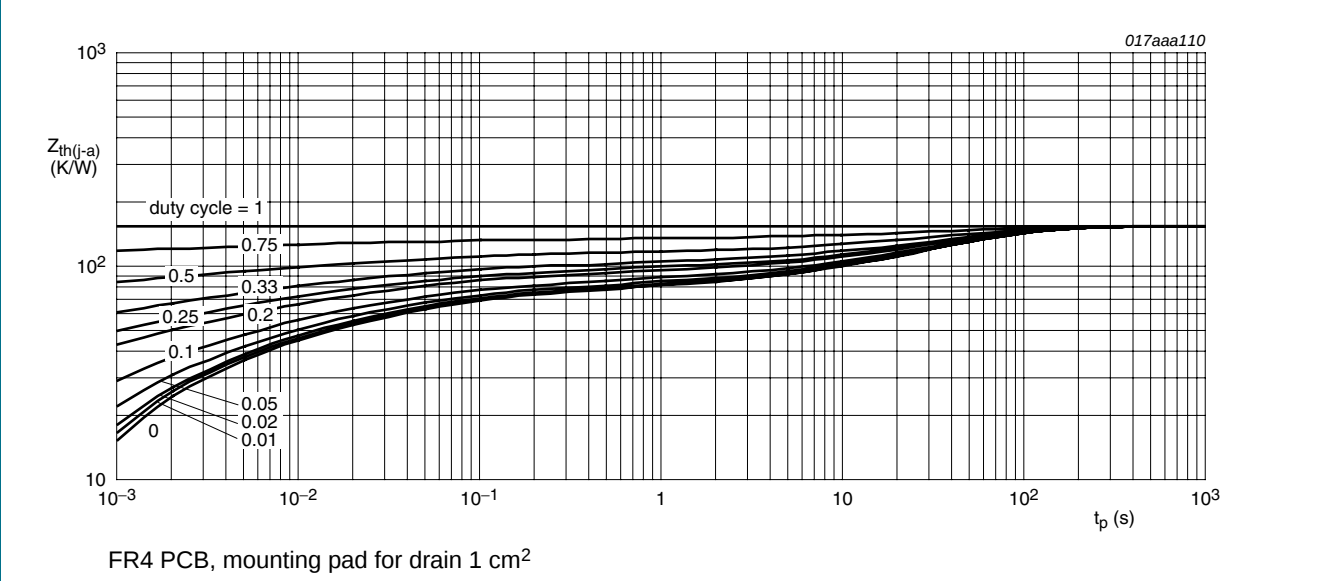


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                  | Min   | Typ   | Max  | Unit |
|-------------------------|----------------------------------|-----------------------------------------------------------------------------------------------------------------------------|-------|-------|------|------|
| Static characteristics  |                                  |                                                                                                                             |       |       |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = -10 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                      | -50   | -     | -    | V    |
| V <sub>GSth</sub>       | gate-source threshold voltage    | I <sub>D</sub> = -250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C                                        | -1.1  | -1.6  | -2.1 | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = -50 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                      | -     | -     | -1   | μA   |
|                         |                                  | V <sub>DS</sub> = -50 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C                                                     | -     | -     | -2   | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                      | -     | -     | -10  | μA   |
|                         |                                  | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                       | -     | -     | -10  | μA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 25 °C                                                   | -     | 4.5   | 7.5  | Ω    |
|                         |                                  | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 150 °C                                                  | -     | 8     | 13.5 | Ω    |
|                         |                                  | V <sub>GS</sub> = -5 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 25 °C                                                    | -     | 5.7   | 8.5  | Ω    |
| g <sub>fs</sub>         | forward transconductance         | V <sub>DS</sub> = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 25 °C                                                   | -     | 150   | -    | mS   |
| Dynamic characteristics |                                  |                                                                                                                             |       |       |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | V <sub>DS</sub> = -25 V; I <sub>D</sub> = -200 mA; V <sub>GS</sub> = -5 V; T <sub>j</sub> = 25 °C                           | -     | 0.26  | 0.35 | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                             | -     | 0.12  | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                             | -     | 0.09  | -    | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>DS</sub> = -25 V; f = 1 MHz; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                           | -     | 24    | 36   | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                             | -     | 4.5   | -    | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                             | -     | 1.3   | -    | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = -30 V; R <sub>L</sub> = 250 Ω; V <sub>GS</sub> = -10 V; R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C | -     | 13    | 26   | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                             | -     | 11    | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                             | -     | 48    | 96   | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                             | -     | 25    | -    | ns   |
| Source-drain diode      |                                  |                                                                                                                             |       |       |      |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = -115 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     | -0.48 | -0.85 | -1.2 | V    |

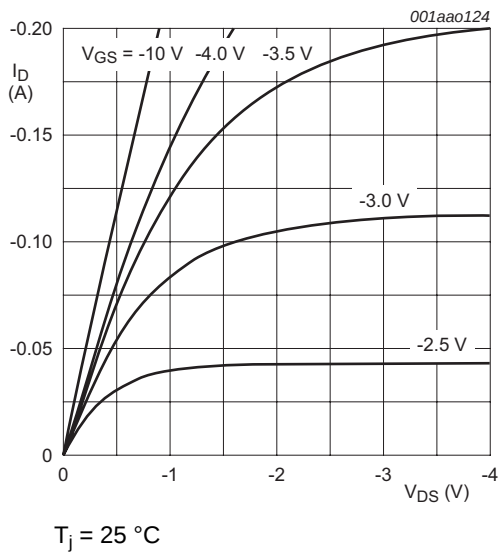


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

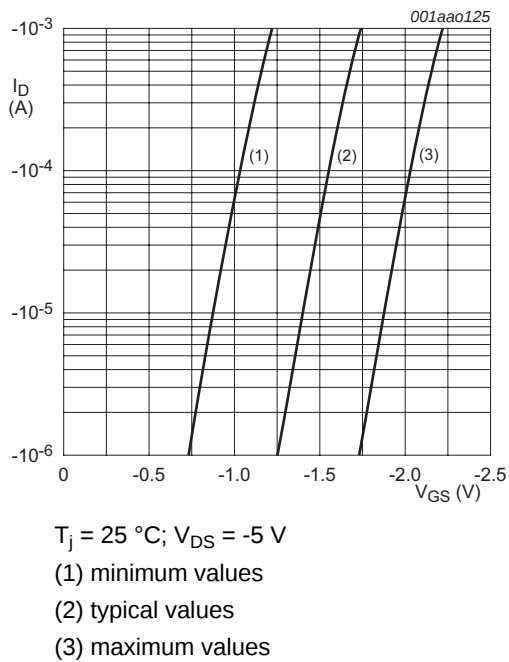


Fig 7. Sub-threshold drain current as a function of gate-source voltage

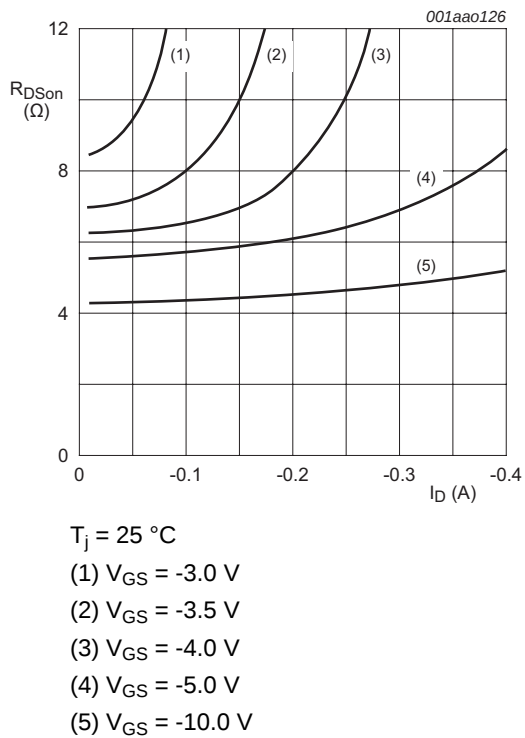


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

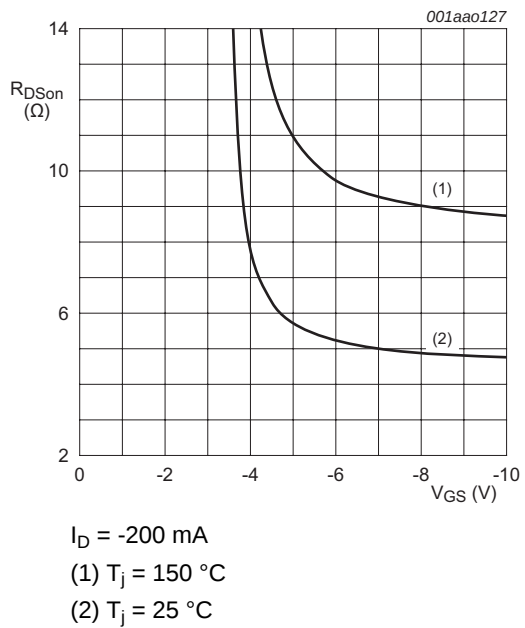
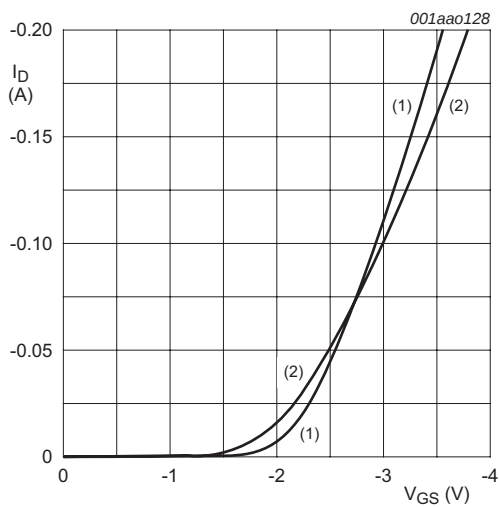
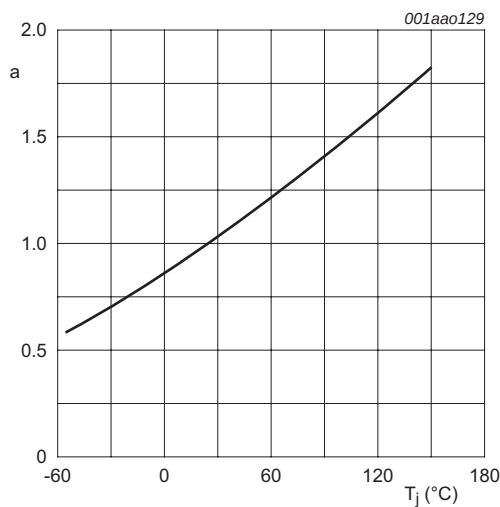


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



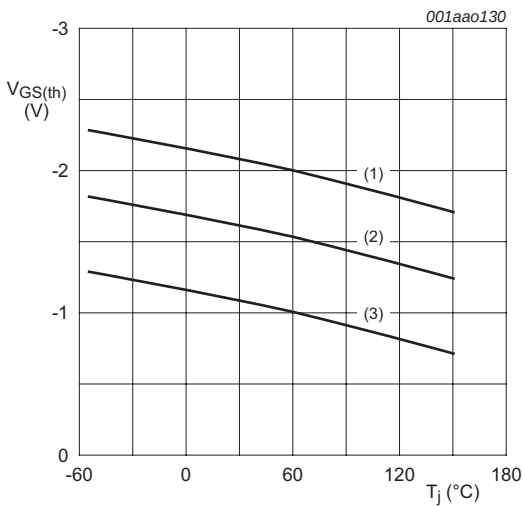
$V_{DS} > I_D \times R_{DSon}$   
(1)  $T_j = 25\text{ }^{\circ}\text{C}$   
(2)  $T_j = 150\text{ }^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



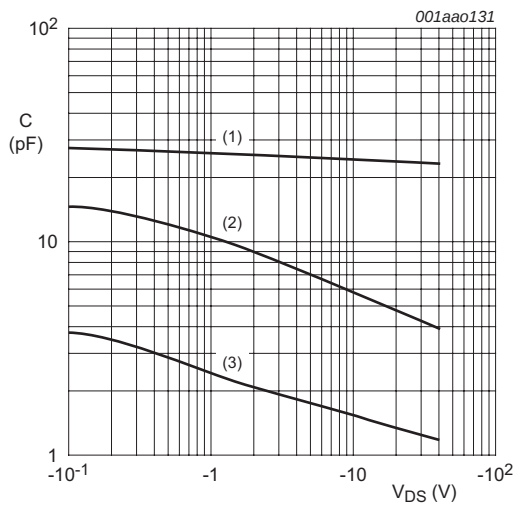
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



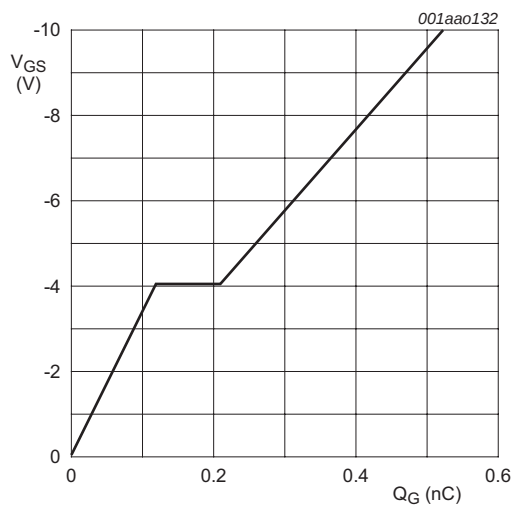
$I_D = -0.25\text{ mA}$ ;  $V_{DS} = V_{GS}$   
(1) maximum values  
(2) typical values  
(3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}$ ,  $V_{GS} = 0\text{ V}$   
(1)  $C_{iss}$   
(2)  $C_{oss}$   
(3)  $C_{rss}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = -0.2$  A;  $V_{DS} = -25$  V;  $T_{amb} = 25$  °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

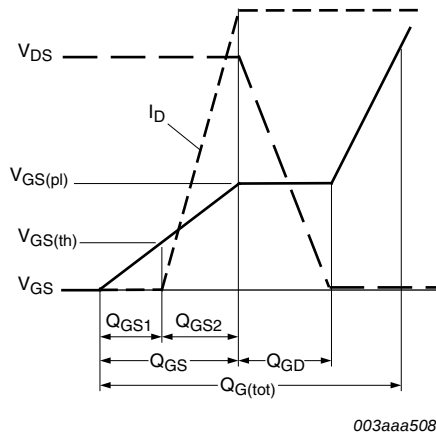
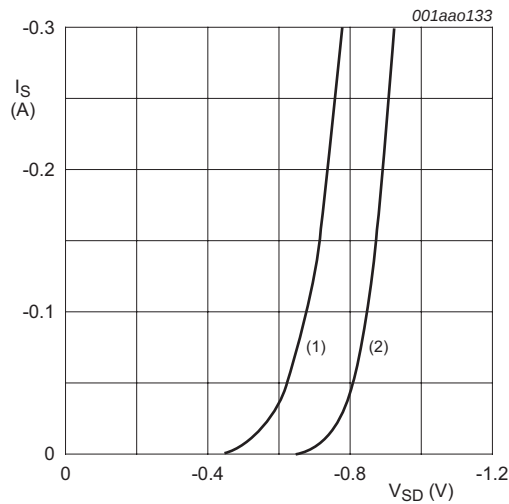


Fig 15. Gate charge waveform definitions



$V_{GS} = 0$  V  
(1)  $T_j = 150$  °C  
(2)  $T_j = 25$  °C

Fig 16. Source current as a function of source-drain voltage; typical values

## 8. Test information

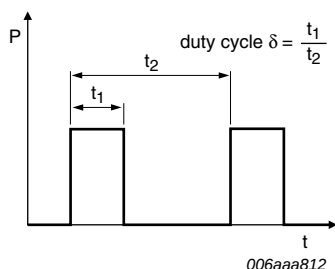


Fig 17. Duty cycle definition

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

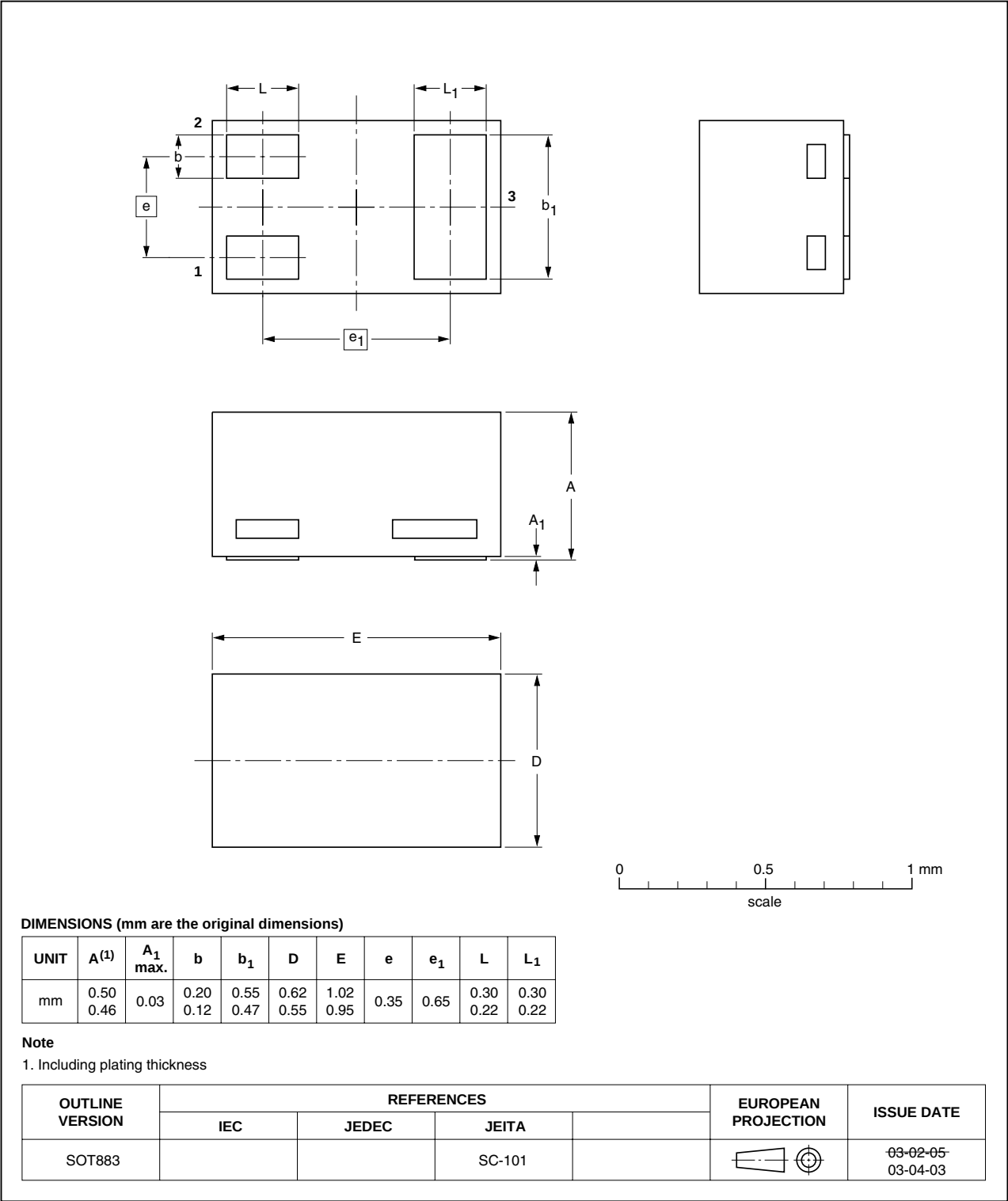


Fig 18. Package outline SOT883 (SOT883)

10. Soldering

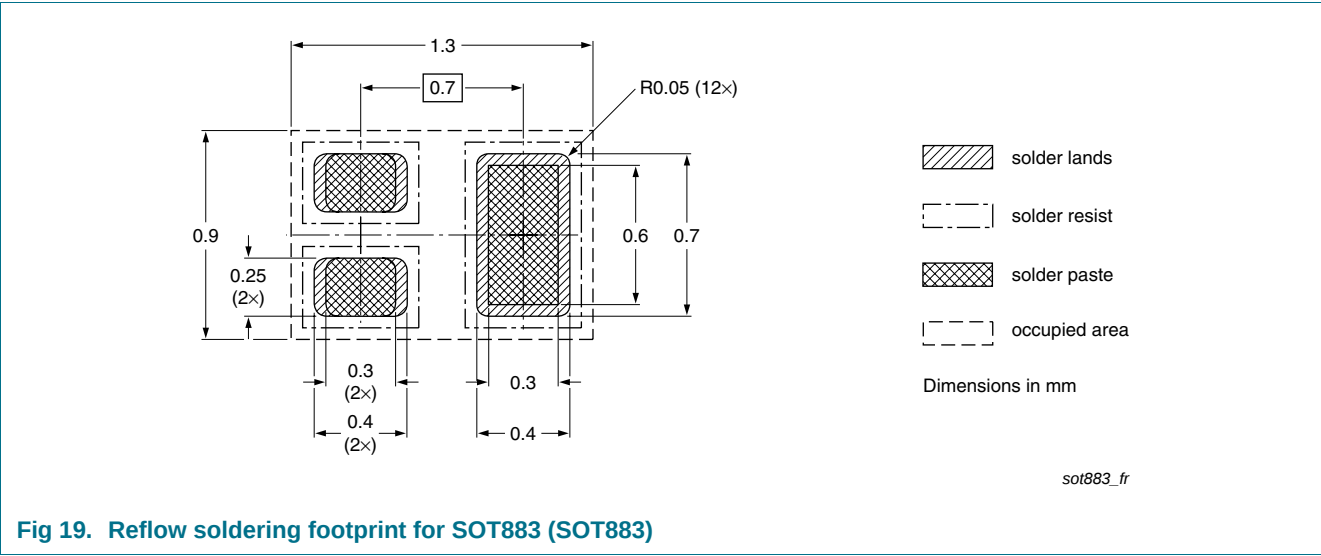


Fig 19. Reflow soldering footprint for SOT883 (SOT883)

11. Revision history

Table 8. Revision history

| Document ID  | Release date | Data sheet status  | Change notice | Supersedes |
|--------------|--------------|--------------------|---------------|------------|
| BSS84AKM v.1 | 20110523     | Product data sheet | -             | -          |

## 12. Legal information

### 12.1 Data sheet status

| Document status <sup>[1]</sup> <sup>[2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|-----------------------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet                  | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet                | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet                    | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## Данный компонент на территории Российской Федерации

**Вы можете приобрести в компании MosChip.**

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

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